Zibo Seno Electronic Engineering Co., Ltd.



MBR4040CT - MBR40200CT





40.0A SCHOTTKY BARRIER DIODE

Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

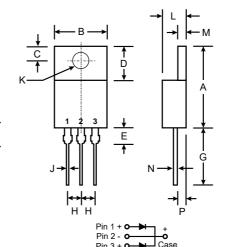
Case: TO-220AB, Molded Plastic

Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208

Polarity: See DiagramMounting Position: Any

Lead Free: For RoHS / Lead Free Version



TO-220AB							
Dim	Min	Max					
Α	14.22	15.88					
В	9.57	10.57					
С	2.54	3.43					
D	5.80	6.80					
E	_	6.35					
G	12.70	14.73					
Н	2.29	2.79					
J	0.51	1.14					
K	3.53Ø	4.14∅					
L	3.56	4.83					
М	1.07	1.47					
N	0.30	0.64					
Р	2.03	2.92					
All Dimensions in mm							

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR 4040 CT	MBR 4045 CT	MBR 4050 CT	MBR 4060 CT	MBR 40100 CT	MBR 40150 CT	MBR 40200 CT	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	40	45	50	60	100	150	200	V
RMS Reverse Voltage	VR(RMS)	28	31	35	42	70	105	140	V
Average Rectified Output Current @T _L = 75°C (Note 1)	lo	40.0						А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	200					А		
Forward Voltage @I _F = 20A	VFM	0.70 0.80			0.85		0.92	V	
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	IRM	0.1 20						mA	
Typical Junction Capacitance (Note 2)	Cj	350 280 20		200	200				
Typical Thermal Resistance (Note 1)	RθJA	3.5 2.0				°C/W			
Operating and Storage Temperature Range	Тj, Tsтg	-55 to +150 -55 to +175				+175	°C		

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

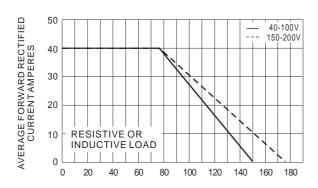
2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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LEAD TEMPERATURE, °C

Fig.1-FORWARD CURRENT DERATING CURVE

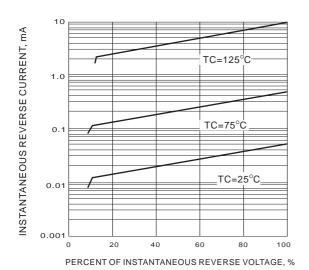


Fig.3-TYPICAL REVERSE CHARACTERISTIC

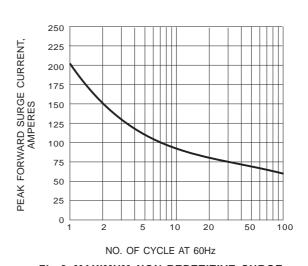
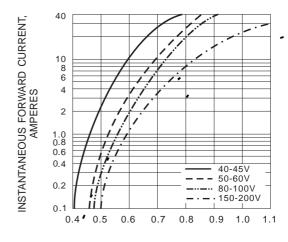


Fig.2-MAXIMUM NON-REPETITIVE SURGE CURRENT



INSTANTANEOUS FORWARD VOLTAGE, VOLTS

Fig.4- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTIC